



N-Channel 650 V (D-S) Super Junction MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$ TYP.	I _D (A)	Q _g (Typ.)
650	0.173 at V _{GS} = 10 V	20	18

TO-252 G D S Top View N-Channel MOSFET

FEATURES

- Super Junction MOSFET
- 100 % R_g and UIS Tested
- Easy to use/drive



APPLICATIONS

- Computing
 - PC silver box / ATX power supplies
- Lighting
 - Two stage LED lighting
- Consumer electronics
- Applications using hard switched topologies
 - Power factor correction (PFC)
 - Two switch forward converter
 - Flyback converter
- Switch mode power supplies (SMPS)

ABSOLUTE MAXIMUM R	ATINGS ($T_C = 25 ^{\circ}C$, unless oth	nerwise noted)			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	650	V		
Gate-Source Voltage		V _{GS}	± 30	V	
Continuous Drain Current	T _C = 25 °C	,	20		
Continuous Diain Current	T _C = 100 °C	I _D	15	A	
Pulsed Drain Current (t = 300 μs)	I _{DM}	72	A		
Avalanche Current		I _{AS}	18.9		
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	57	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	P _D	97 ^b	W	
	T _A = 25 °C°		2.1	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	65	°C/W	
Junction-to-Case (Drain)	R _{thJC}	2	C/VV	

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Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Base on T_C = 25 °C.

Rev. 1.0



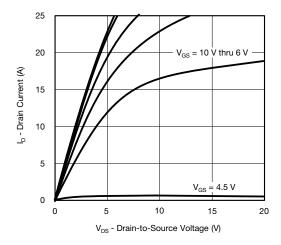
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	•					
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	650			4 V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current		V _{DS} = 650 V, V _{GS} = 0 V			1	μA
	I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 650 V, V _{GS} = 0 V, T _J = 150 °C			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α
Drain-Source On-State Resistance ^a	В	V _{GS} = 10 V, I _D = 5 A,TJ= 25 °C		0.173	0.195	Ω
	R _{DS(on)}	V _{GS} = 10 V, I _D = 5 A,TJ= 150 °C		0.438		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 5 A		15		S
Dynamic ^b						
Input Capacitance	C _{iss}			1010		pF
Output Capacitance	C _{oss}	V _{DS} = 400 V, V _{GS} = 0 V, f = 1 MHz		25		
Reverse Transfer Capacitance	C _{rss}			11		
Total Gate Charge ^c	Qg			18		nC
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 400 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 5 \text{ A}$		6.6		
Gate-Drain Charge ^c	Q_{gd}			8.1		
Gate Resistance	R _g	f = 1 MHz		1.5		Ω
Turn-On Delay Time ^c	t _{d(on)}			8		
Rise Time ^c	t _r	$V_{DD} = 400 \text{ V}, R_{L} = 9.6 \Omega$		11		ns
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 5.2 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 10\Omega$		18		
Fall Time ^c	t _f			5		
Drain-Source Body Diode Ratings ar	nd Characteri	stics ^b T _C = 25 °C				
Continuous Current	I _S				20	А
Pulsed Current	I _{SM}				72	
Forward Voltage ^a	V _{SD}	I _F = 5 A, V _{GS} = 0 V		0.9		V
Reverse Recovery Time	t _{rr}			926		ns
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = 5 A, dI/dt = 100 A/μs		22		Α
Reverse Recovery Charge	Q _{rr}			6		μC

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing. c. Independent of operating temperature.

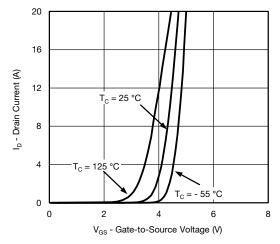
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



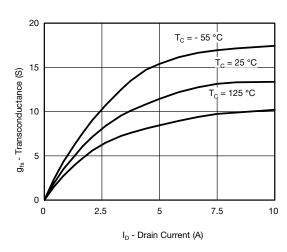
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



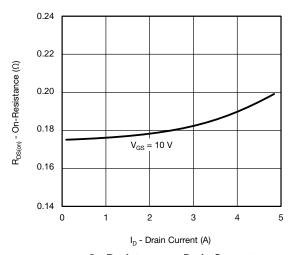
Output Characteristics



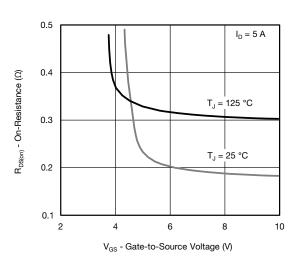
Transfer Characteristics



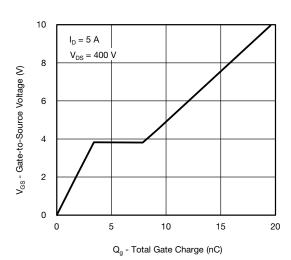
Transconductance



On-Resistance vs. Drain Current



On-Resistance vs. Gate-to-Source Voltage

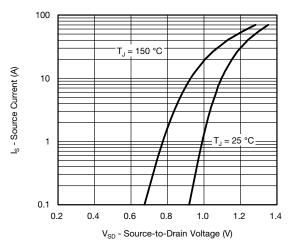


Gate Charge

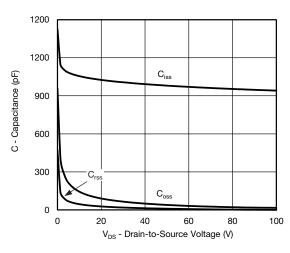




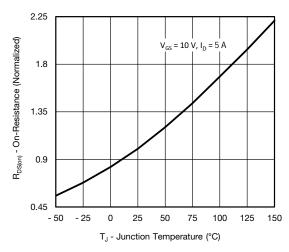
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



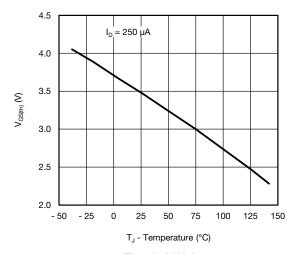
Source-Drain Diode Forward Voltage



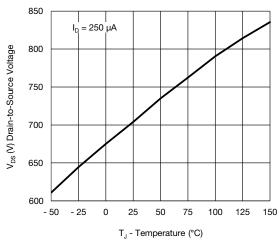
Capacitance



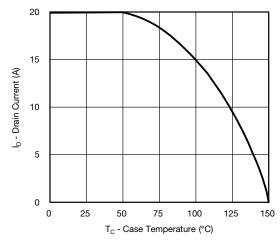
On-Resistance vs. Junction Temperature



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

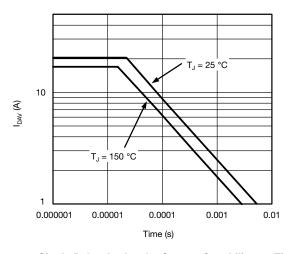


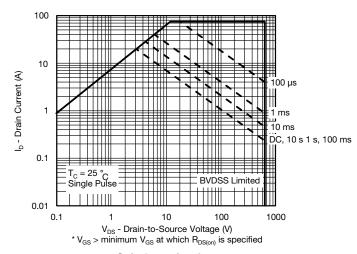
Current Derating





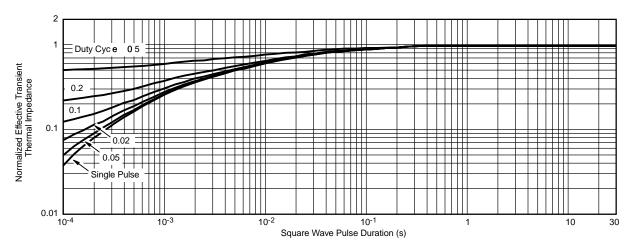
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Single Pulse Avalanche Current Capability vs. Time





Normalized Thermal Transient Impedance, Junction-to-Case





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